

Accepted Manuscript

New GaN based HEMT with Si_3N_4 or un-doped region in the barrier for high power applications

S.M. Razavi, S. Tahmasb Pour, P. Najari

PII: S0749-6036(18)30513-5

DOI: [10.1016/j.spmi.2018.04.019](https://doi.org/10.1016/j.spmi.2018.04.019)

Reference: YSPMI 5633

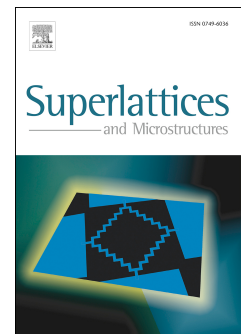
To appear in: *Superlattices and Microstructures*

Received Date: 14 March 2018

Accepted Date: 9 April 2018

Please cite this article as: S.M. Razavi, S. Tahmasb Pour, P. Najari, New GaN based HEMT with Si_3N_4 or un-doped region in the barrier for high power applications, *Superlattices and Microstructures* (2018), doi: 10.1016/j.spmi.2018.04.019.

This is a PDF file of an unedited manuscript that has been accepted for publication. As a service to our customers we are providing this early version of the manuscript. The manuscript will undergo copyediting, typesetting, and review of the resulting proof before it is published in its final form. Please note that during the production process errors may be discovered which could affect the content, and all legal disclaimers that apply to the journal pertain.



New GaN based HEMT with Si_3N_4 or un-doped region in the barrier for high power applications

S. M. Razavi^{1*}, S. Tahmasb Pour^{*} and P. Najari^{*}

^{*}Department of Electrical Engineering, University of Neyshabur, Neyshabur, Iran

¹Corresponding author email: razavi@neyshabur.ac.ir

Download English Version:

<https://daneshyari.com/en/article/7938739>

Download Persian Version:

<https://daneshyari.com/article/7938739>

[Daneshyari.com](https://daneshyari.com)